

- ★ Green Device Available
- ★ Super Low Gate Charge
- ★ Excellent CdV/dt effect decline
- ★ Advanced high cell density Trench technology

Product Summary



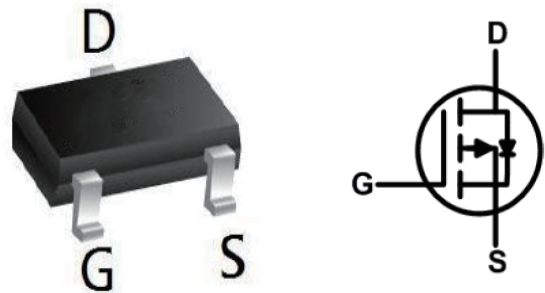
BVDSS	RDS(ON)	ID
-20V	95mΩ	-2.3A

Description

The 2301V is the high cell density trenched P-ch MOSFETs, which provide excellent RDS(ON) and efficiency for most of the small power switching and load switch applications.

The 2301V meet the RoHS and Green Product requirement with full function reliability approved.

SOT23 Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	-20	V
$V_{GS}$	Gate-Source Voltage	±12	V
$I_{D@T_A=25^{\circ}C}$	Continuous Drain Current, $V_{GS} @ 10V^1$	-2.3	A
$I_{D@T_A=70^{\circ}C}$	Continuous Drain Current, $V_{GS} @ 10V^1$	-1.4	A
$I_{DM}$	Pulsed Drain Current <sup>2</sup>	-8	A
$P_{D@T_A=25^{\circ}C}$	Total Power Dissipation <sup>3</sup>	0.8	W
$T_{STG}$	Storage Temperature Range	-55 to 150	°C
$T_J$	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient <sup>1</sup>	---	156	°C/W
$R_{\theta JC}$	Thermal Resistance Junction-Case <sup>1</sup>	---	---	°C/W

**Electrical Characteristics (T<sub>J</sub> =25 °C unless otherwise specified)**

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
<b>Off Characteristic</b>						
V <sub>(BR)DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> =0V, I <sub>D</sub> = -250μA	-20	-	-	V
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = -20V, V <sub>GS</sub> = 0V,	-	-	-1	μA
I <sub>GSS</sub>	Gate to Body Leakage Current	V <sub>DS</sub> =0V, V <sub>GS</sub> = ±12V	-	-	±100	nA
<b>On Characteristics</b>						
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = -250μA	-0.4	-0.7	-1	V
R <sub>DS(on)</sub>	Static Drain-Source on-Resistance note2	V <sub>GS</sub> =-4.5V, I <sub>D</sub> =-2A	-	95	125	mΩ
		V <sub>GS</sub> =-2.5V, I <sub>D</sub> =-1A	-	135	190	
<b>Dynamic Characteristics</b>						
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = -10V, V <sub>GS</sub> = 0V, f = 1.0MHz	-	185	-	pF
C <sub>oss</sub>	Output Capacitance		-	35	-	pF
C <sub>rss</sub>	Reverse Transfer Capacitance		-	25	-	pF
Q <sub>g</sub>	Total Gate Charge	V <sub>DS</sub> = -10V, I <sub>D</sub> = -2A, V <sub>GS</sub> = -4.5V	-	2.2	-	nC
Q <sub>gs</sub>	Gate-Source Charge		-	0.5	-	nC
Q <sub>gd</sub>	Gate-Drain( "Miller" ) Charge		-	0.5	-	nC
<b>Switching Characteristics</b>						
t <sub>d(on)</sub>	Turn-on Delay Time	V <sub>DD</sub> = -10V, R <sub>L</sub> =5 Ω, R <sub>GEN</sub> =3 Ω, V <sub>GS</sub> =-4.5V,	-	10	-	ns
t <sub>r</sub>	Turn-on Rise Time		-	30	-	ns
t <sub>d(off)</sub>	Turn-off Delay Time		-	63	-	ns
t <sub>f</sub>	Turn-off Fall Time		-	50	-	ns
<b>Drain-Source Diode Characteristics and Maximum Ratings</b>						
I <sub>S</sub>	Maximum Continuous Drain to Source Diode Forward Current		-	-	-2	A
I <sub>SM</sub>	Maximum Pulsed Drain to Source Diode Forward Current		-	-	-8	A
V <sub>SD</sub>	Drain to Source Diode Forward Voltage	V <sub>GS</sub> = 0V, I <sub>S</sub> = -2A	-	-	-1.2	V

**Note :**

1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature
2. Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%

Typical Performance Characteristics

Figure 1: Output Characteristics

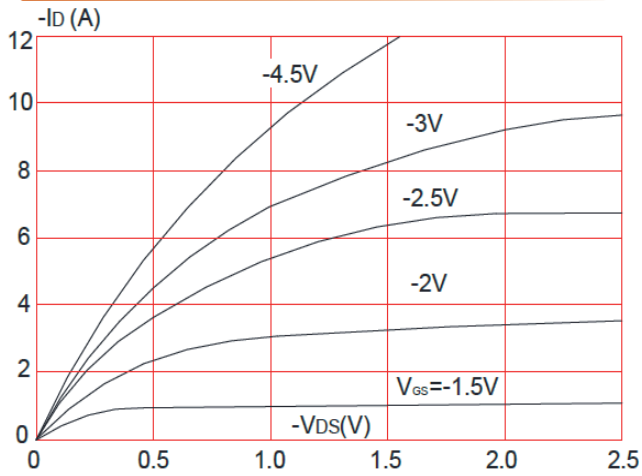


Figure 2: Typical Transfer Characteristics

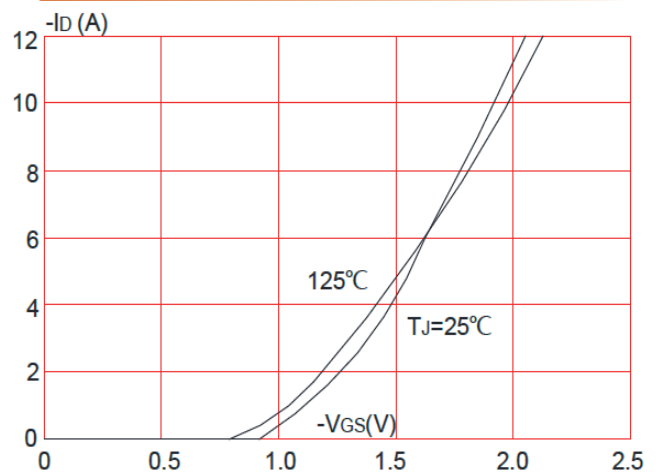


Figure 3: On-resistance vs. Drain Current

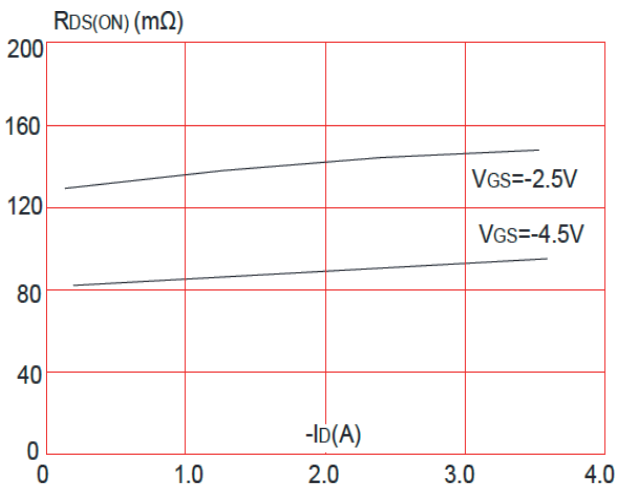


Figure 4: Body Diode Characteristics

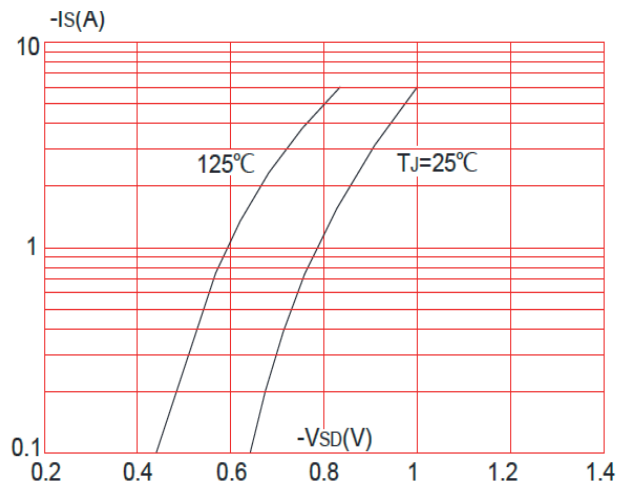


Figure 5: Gate Charge Characteristics

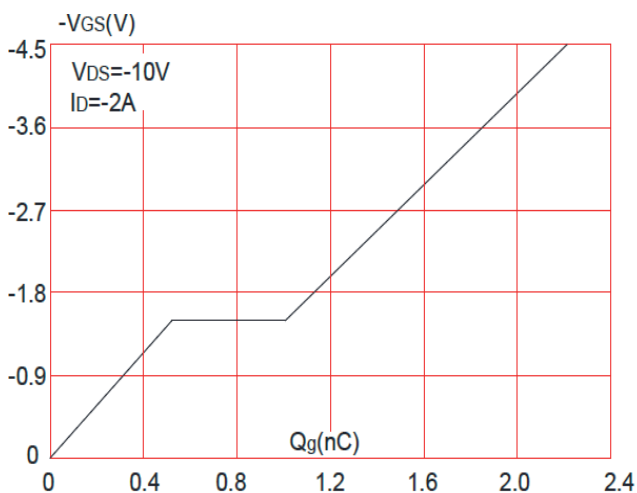
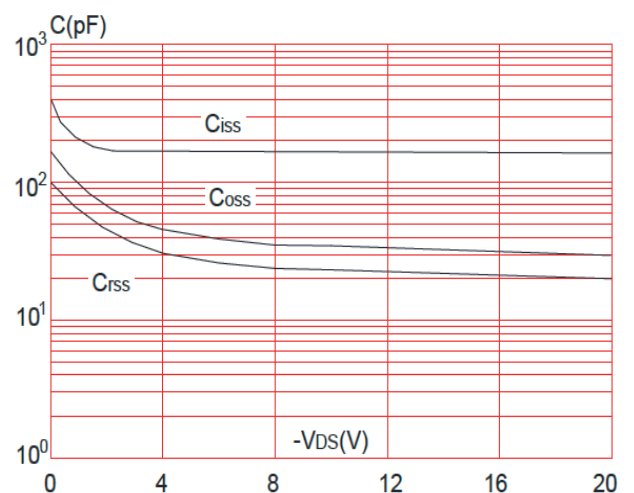


Figure 6: Capacitance Characteristics



Typical Performance Characteristics

Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

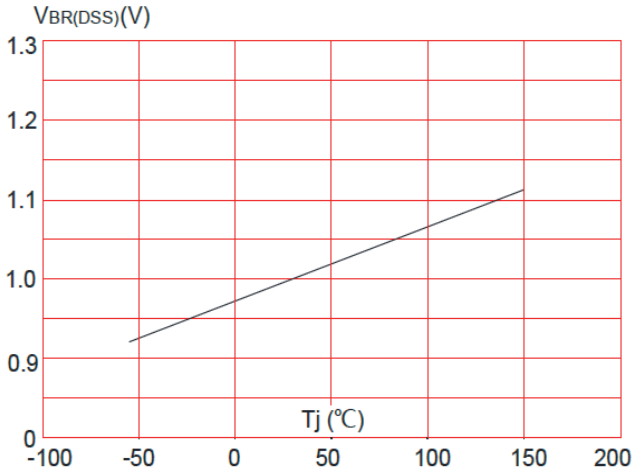


Figure 8: Normalized on Resistance vs. Junction Temperature

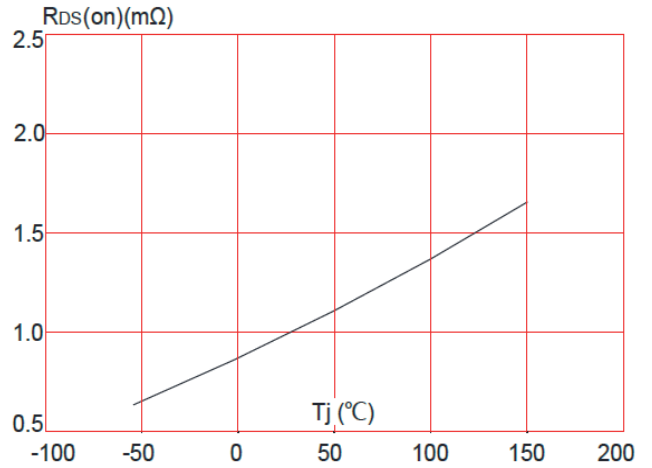


Figure 9: Maximum Safe Operating Area

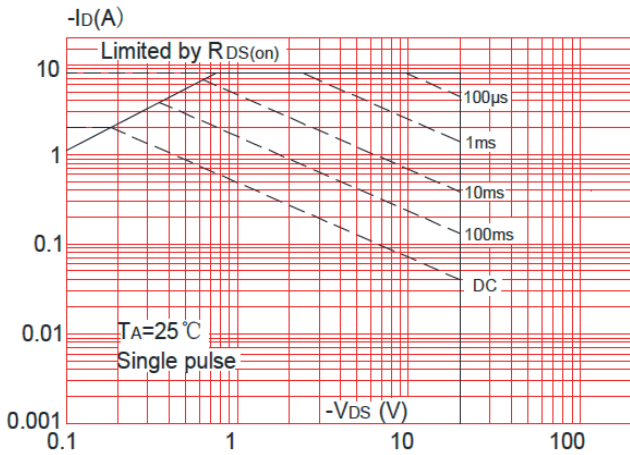


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

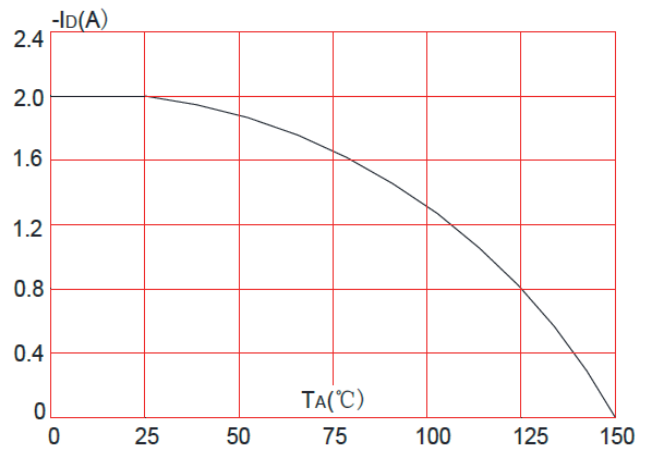
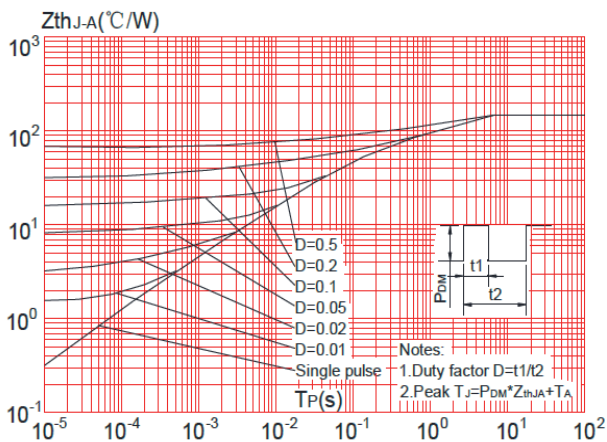
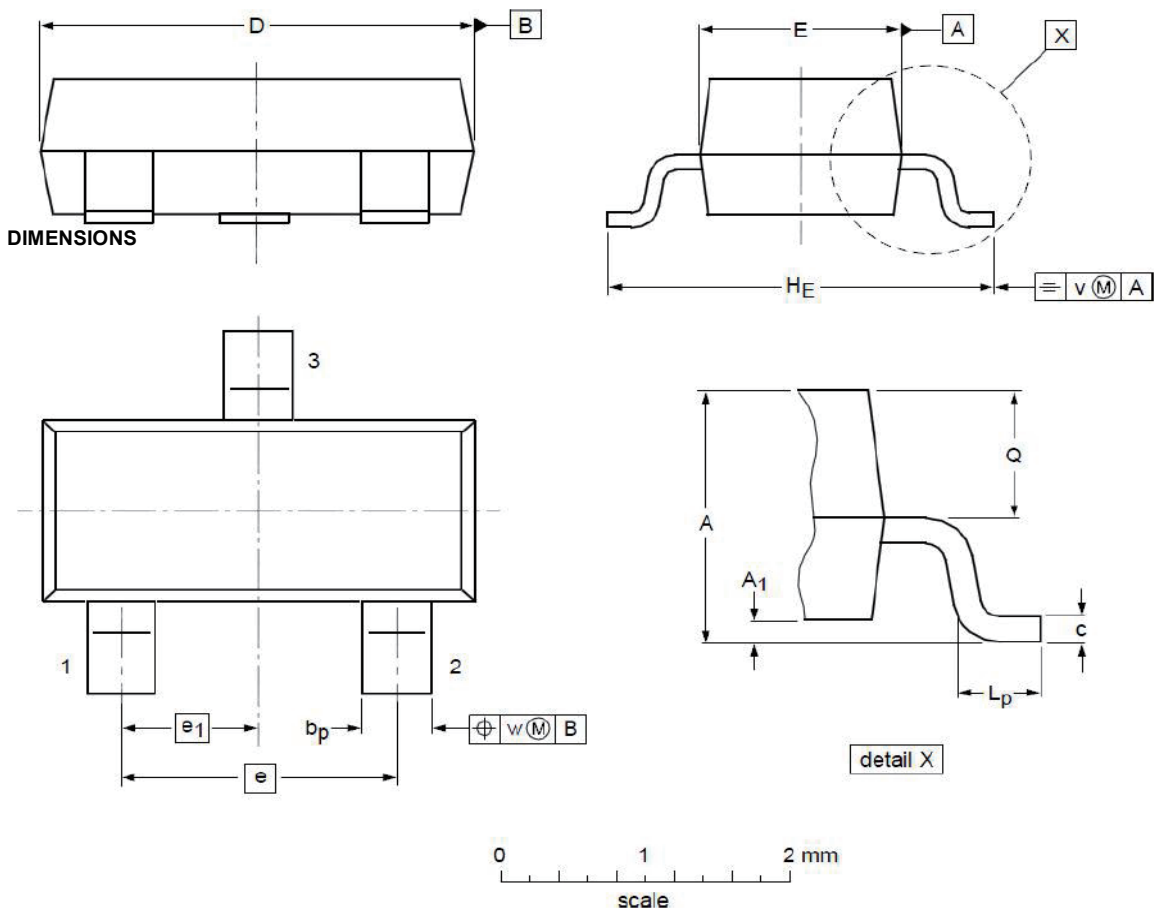


Figure 11: Maximum Effective Transient Thermal Impedance Junction to Ambient



SOT23 Mechanical tData



DIMENSIONS ( unit : mm )

Symbol	Min	Typ	Max	Symbol	Min	Typ	Max
A	0.9	1.01	1.15	A <sub>1</sub>	0.01	0.05	0.1
b <sub>p</sub>	0.3	0.42	0.5	c	0.08	0.13	0.15
D	2.8	2.92	3	E	1.2	1.33	1.4
e	--	1.9	--	e <sub>1</sub>	--	0.95	--
H <sub>E</sub>	2.25	2.4	2.55	L <sub>p</sub>	0.3	0.42	0.5
Q	0.45	0.49	0.55	v	--	0.2	--
w	--	0.1	--				